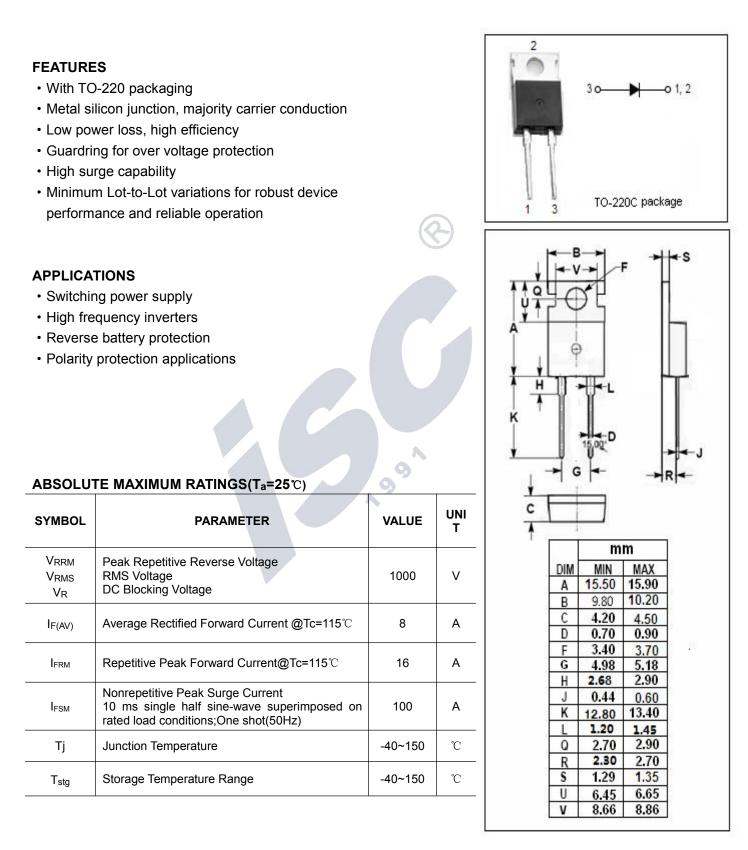


Ultra fast Rectifier

INCHANGE SEMICONDUCTOR

BYT08P-1000



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Ultra fast Rectifier

BYT08P-1000

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2	°C/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
VF	Maximum Instantaneous Forward Voltage	I _F = 8A;Tc= 25°C I _F = 8A;Tc= 100°C	1.9 1.8	V
IR	Maximum Instantaneous Reverse Current	V _R = rated V _{RRM;} Tc= 25°C Tc=100°C	35 2000	μA
trr	Maximum Reverse Recovery Time	l⊧ =1A;dl⊧/dt=-15A/ μ s;V _R =30V	155	ns

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